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SEMICONDUCTOR®

FDP7N50 N-Channel UniFETTM MOSFET 500 V, 7 A, 900 mΩ

500 V, I A, 900

Features

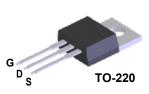
- + $R_{DS(on)}$ = 900 m Ω (Max.) @ V_{GS} = 10 V, I_D = 3.5 A
- Low Gate Charge (Typ. 12.8 nC)
- Low C_{rss} (Typ. 9 pF)
- 100% Avalanche Tested

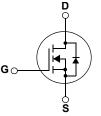
Applications

- ALCD/LED TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supplypplications

Description

UniFETTM MOSFET is Fairchild Semiconductor[®], s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings

Symbol	Parameter			FDP7N50	Unit	
V _{DSS}	Drain-Source Voltage			500	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$ - Continuous ($T_C = 100^{\circ}$			7 4.2	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	28	A	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	270	mJ	
I _{AR}	Avalanche Current		(Note 1)	7	A	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	8.9	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		89 0.71	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
Τ _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		e,	300	°C	

Thermal Characteristics

Symbol	Parameter	FDP7N50	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.4	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	

April 2013

DP7N50
N-Channel
UniFET TM
MOSFET

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP7N50	FDP7N50	TO-220			50

Electrical Characteristics T_c = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$			1 10	μΑ μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics				1	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 3.5A		0.76	0.9	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 40V, I_D = 3.5A$			2.5		S
Dynamic C	haracteristics				1	
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,		720	940	pF
C _{oss}	Output Capacitance	f = 1.0MHz		95	190	pF
C _{rss}	Reverse Transfer Capacitance			9	13.5	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 7A		6	20	ns
t _r	Turn-On Rise Time	$R_{G} = 25\Omega$		55	120	ns
t _{d(off)}	Turn-Off Delay Time			25	60	ns
t _f	Turn-Off Fall Time	(Note 4)		35	80	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 7A		12.8	16.6	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V		3.7		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		5.8		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings		1	1	
I _S	Maximum Continuous Drain-Source Diode Forward Current				7	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				28	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 7A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 7A		275		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		1.7		μC

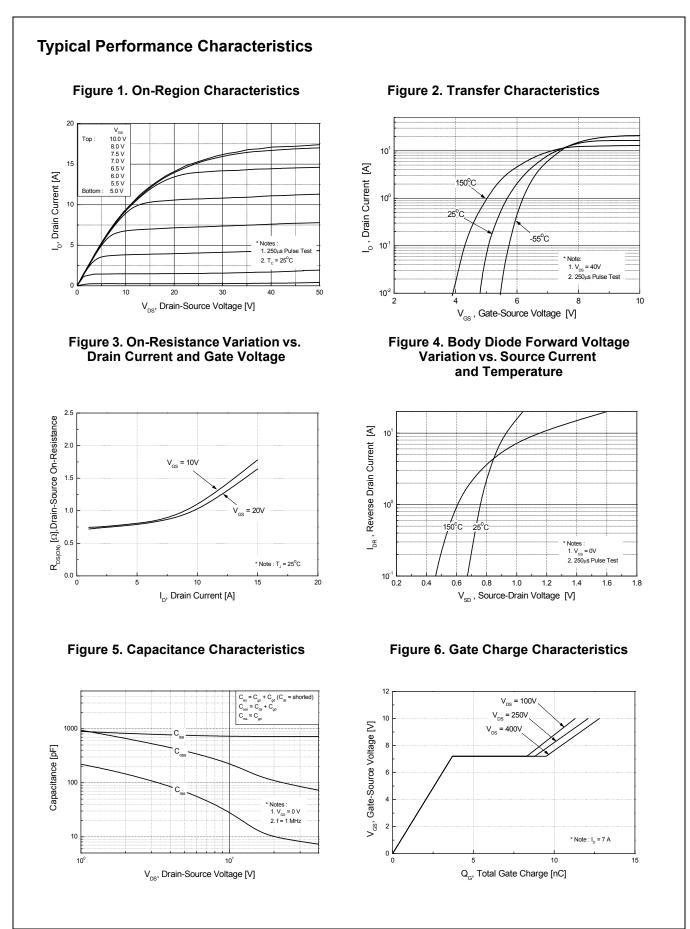
NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

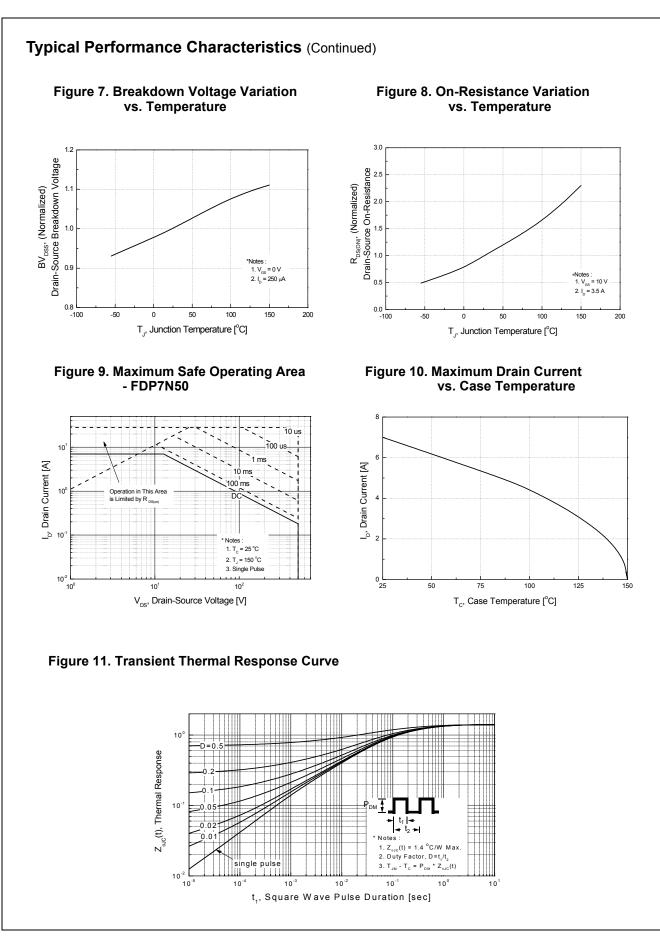
2. I_{AS} = 7A, V_{DD} = 50V, L=10mH, R_G = 25 Ω , Starting T_J = 25°C

3. I_{SD} \leq 7A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

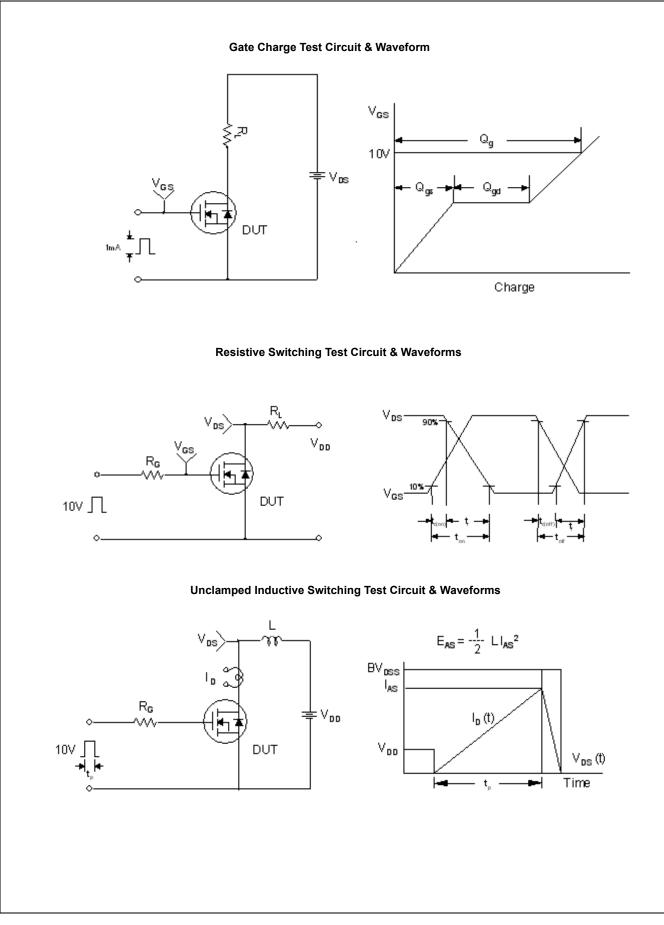
4. Essentially Independent of Operating Temperature Typical Characteristics



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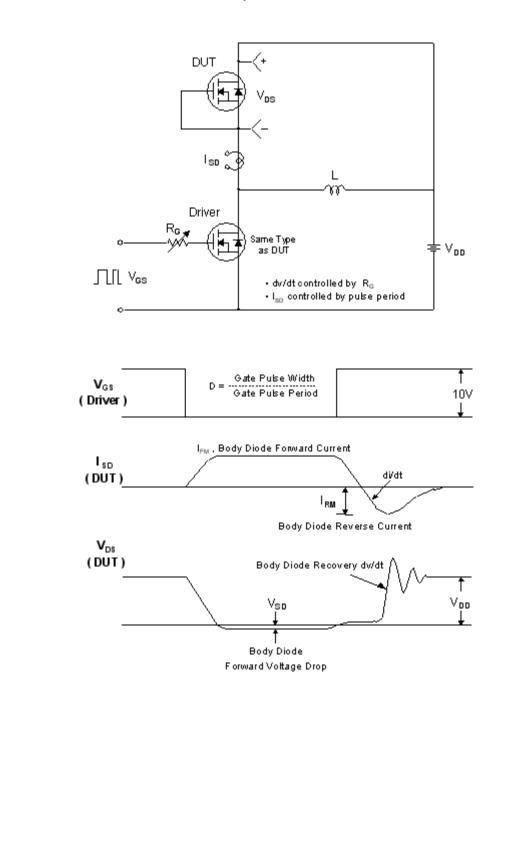


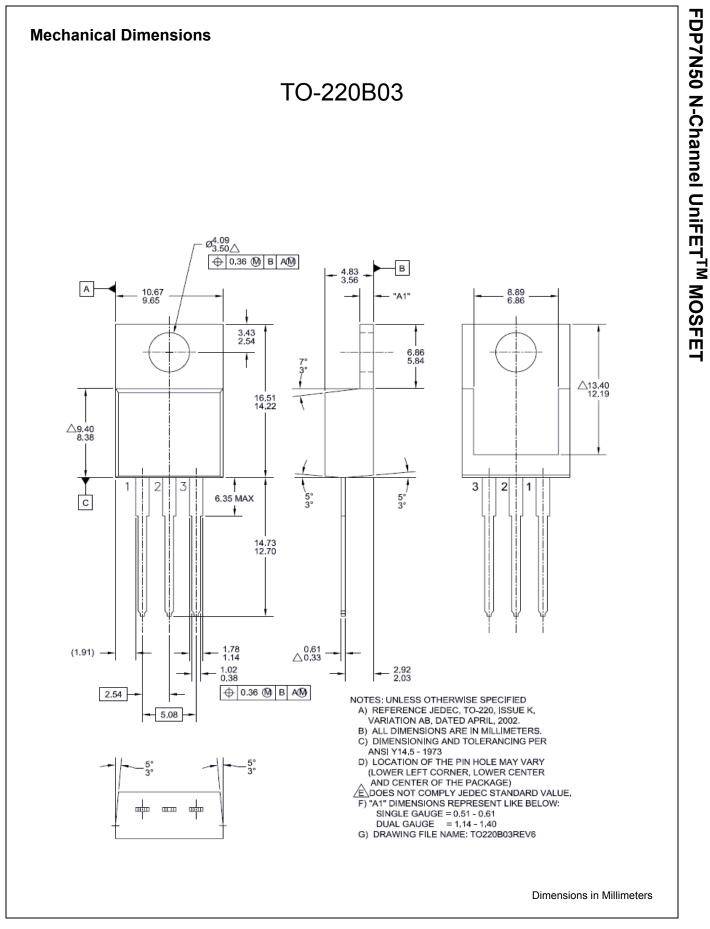
FDP7N50 N-Channel UniFETTM MOSFET



FDP7N50 N-Channel UniFETTM MOSFET

Peak Diode Recovery dv/dt Test Circuit & Waveforms







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